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PTO/SB/21 (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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**TRANSMITTAL
FORM**

(to be used for all correspondence after initial filing)

TRANSMITTAL FORM (to be used for all correspondence after initial filing)	Application Number	10/797,239	
	Filing Date	March 9, 2004	
	First Named Inventor	Alan J. Heeger, et al.	
	Group Art Unit	2997	
	Examiner Name	Not Yet Assigned	
Total Number of Pages in This Submission		Attorney Docket Number	1279-404XX/10303106

ENCLOSURES (check all that apply)

<input type="checkbox"/> Fee Transmittal Form <input type="checkbox"/> Fee Attached <input type="checkbox"/> Amendment/Reply <input type="checkbox"/> After Final <input type="checkbox"/> Affidavits/declaration(s) <input type="checkbox"/> Extension of Time Request <input type="checkbox"/> Express Abandonment Request <input checked="" type="checkbox"/> Information Disclosure Statement <input type="checkbox"/> Certified Copy of Priority Document(s) <input type="checkbox"/> Response to Missing Parts/Incomplete Application <input type="checkbox"/> Response to Missing Parts under 37 CFR 1.52 or 1.53	<input type="checkbox"/> Assignment Papers (for an Application) <input type="checkbox"/> Drawing(s) <input type="checkbox"/> Licensing-related Papers <input type="checkbox"/> Petition <input type="checkbox"/> Petition to Convert to a Provisional Application <input type="checkbox"/> Power of Attorney, Revocation Change of Correspondence Address <input type="checkbox"/> Terminal Disclaimer <input type="checkbox"/> Request for Refund <input type="checkbox"/> CD, Number of CD(s) _____	<input type="checkbox"/> After Allowance Communication to Group <input type="checkbox"/> Appeal Communication to Board of Appeals and Interferences <input type="checkbox"/> Appeal Communication to Group (Appeal Notice, Brief, Reply Brief) <input type="checkbox"/> Proprietary Information <input type="checkbox"/> Status Letter <input checked="" type="checkbox"/> Other Enclosure(s) (please identify below) 1. PTO-1449 FORM (SB/08B) 2. CITED ARTICLES; 3. POSTCARD
Remarks		

SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT

Firm or Individual Name	FULBRIGHT & JAWORSKI L.L.P. Robert Berliner
Signature	
Date	September 10, 2004

Transmittal of Information Disclosure Statement

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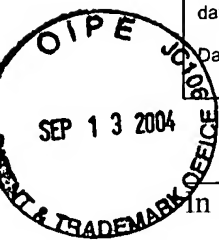
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Signature:

Aide G. Silva
(Aide G. Silva)

Docket No.: 1279-404XX
(PATENT)



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Alan J. Heeger, et al.

Application No.: 10/797,239

Filed: March 9, 2004

For: **INJECTION LASERS FABRICATED
FROM SEMICONDUCTING POLYMERS**

) Confirmation No.: 2997

) Art Unit: 2811

) Examiner: Not Yet Assigned

INFORMATION DISCLOSURE STATEMENT (IDS)

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Dear Sir:

Pursuant to 37 CFR 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is filed, as far as is known to the undersigned, before the mailing date of a first Office Action on the merits as far as is known to the undersigned (37 CFR 1.97(b)(3)). No certification or fee is required.

A copy of each cited article on the PTO/SB/08 is attached.

In accordance with 37 CFR 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information

as defined in 37 CFR 1.56(a) exists. In accordance with 37 CFR 1.97(h), the filing of this Information Disclosure statement shall not be construed to be an admission that any patent, publication or other information referred to therein is "prior art" for this invention unless specifically designated as such.

It is submitted that the Information Disclosure Statement is in compliance with 37 CFR 1.98 and the Examiner is respectfully requested to consider the listed references.

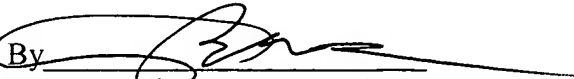
A concise explanation of relevance of the items listed on form PTO/SB/08 is:

- ☒ [X] not given
- ☐ [] given for each listed item
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- ☐ [] in the form of an English language copy of a Search Report from a foreign patent office, issued in a counterpart application, which refers to the relevant portions of the references

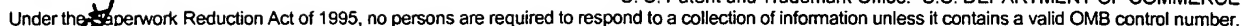
The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 50-0337, under Order No. 1279-404XX/10303106. A duplicate copy of this paper is enclosed.

Dated: September 10, 2004

Respectfully submitted,

By 
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Attorney for Applicant

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	1	of	2
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Complete if Known

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Examiner Name	Not Yet Assigned
Attorney Docket Number	1279-404XX/10303106

U.S. PATENT DOCUMENTS

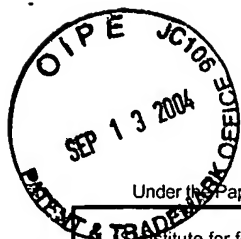
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
	AA	5,237,582	08-17-1993	MOSES	
	AB	5,881,083	03-09-1999	DIAZ-GARCIA, ET AL.	
	AC				
	AD				
	AE				
	AF				

FOREIGN PATENT DOCUMENTS

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Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
	BA					
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	CA	"Polymer Light-Emitting Electrochemical Cells", By QIBING PEI, et al.; <i>Science</i> , Vol. 269, August 25, 1995, pg. 1086	
	CB	"Femtosecond Relaxation of Photoexcitations in a Poly (Para-Phenylene)-Type Ladder Polymer", By W. GRAUPNER, G. LEISING et al.; <i>Physical Review Letters</i> , Vol. 76, No. 5, January 29, 1996; pg. 847	
	CC	"Laser Emission from Solutions and Films Containing Semiconducting Polymer and Titanium Dioxide Nanocrystals", By FUMITOMO HIDE, BENJAMIN J. SCHWARTZ, et al.; <i>Chemical Physics Letters</i> 256 (1996) 424-430; July 5, 1996	
	CD	"Semiconducting Polymers: A New Class of Solid-State Laser Materials", By FUMITOMO HIDE, MARIA A. DIAZ-GARCIA, et al.; <i>Science</i> , Reprint Series, Sept. 27, 1996, Vol. 273, pp. 1833-1836	
	CE	"Polymer Light-Emitting Electrochemical Cells; In Situ Formation of a Light-Emitting p-n Junction", By QIBING PEI, YANG YAN, GANG YU, et al.; <i>J. American Chemical Society</i> , 1996, 118, 3922-3929	
	CF	"Cooperative Emission in π -Conjugated Polymer Thin Films", By S.V. FROLOV, W. GELLERMANN, M. OZAKI, et al.; <i>Physical Review Letters</i> , Vol. 78, No. 4, January 27, 1997, pp. 729-732	
	CG	"'Plastic' Lasers: Comparison of Gain Narrowing with a Soluble Semiconducting Polymer in Waveguides and Microcavities", By MARIA A. DIAZ-GARCIA, FUMITOMO HIDE, et al.; <i>1997 American Institute of Physics</i> , Appl. Phys. Lett. 70 (24), June 16, 1997, pp 3191.	
	CH	"Polymer Light-Emitting Electrochemical Cells with Frozen p-i-n Junction", By JUN GAO, GANG YU, ALAN J. HEEGER, et al.; <i>1997 American Institute of Physics</i> , Appl. Phys. Lett. 71	



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Sheet	2	of	2		

		(10), Sept. 8, 1997, pp. 1293.	
CI		"Peak Current Density and Brightness from Poly (<i>p</i> -phenylenevinylene) Based Light Emitting Diodes", By N.T. HARRISON, N. TESSLER, C.J. MOSS, K. PICHLER, R.H. FRIEND; <i>Optical Materials</i> 9 (1998) 178-182, January 1998	
CJ		"High Peak Brightness Polymer Light-Emitting Diodes", By N. TESSLER, N.T. HARRISON, RICHARD H. FRIEND; <i>Advanced Materials</i> 1998, 10, No. 1, pp. 64.	
CK		"Polymer Light-Emitting Electrochemical Cells with Frozen p-i-n Junction at Room Temperature", By GANG YU, YONG CAO, MATS ANDERSON, JUN GAO and ALAN J. HEEGER; <i>Advanced Materials</i> , 1998, Vol. 10, No. 5, pp. 385.	
CL		"Amplified Spontaneous Emission from Photopumped Films of a Conjugated Polymer", By McGEHEE, GUPTA, VEENSTRA, MILLER, DIAZ-GARCIA, and HEEGER; <i>Physical Review B</i> , Volume 58, No. 11, Sept. 15, 1998, pp. 7035.	
CM		"Low-Threshold Amplified Spontaneous Emission in Blends of Conjugated Polymers", By R. GUPTA, M. STEVENSON, A. DOGARIU, M.D. McGEHEE, J.Y. PARK, V. SRDANOV and A.J. HEEGER; <i>Applied Physics Letters</i> , Volume 73, No. 24, December 14, 1998, pp. 3492	
CN		"Structures for Organic Diode Lasers and Optical Properties of Organic Semiconductors Under Intense Optical and Electrical Excitations", By V.G. KOZLOV, G. PARTHASARATHY, et al.; <i>IEEE Journal of Quantum Electronics</i> , Vol. 36, No. 1, January 2000.	
CO		"Semiconducting (Conjugated) Polymers as Materials for Solid-State Lasers", By M.D. McGEHEE and A.J. HEEGER; <i>Advanced Materials</i> , 2000, Vol. 12, No. 22, November 16, 2000, pp. 1655 - 1668.	
CP		"Synthesis of Soluble Phenyl-Substituted Poly (<i>p</i> -phenylenevinylene)s with a Low Content of Structural Defects", By D.M. JOHANSSON, X. WANG, T. JOHANSSON, et al.; <i>Macromolecules</i> , 2002, Vol. 35, No. 13, 4997-5003	
CQ		"Single-Component Light-Emitting Electrochemical Cell with Improved Stability", By L. EDMAN, M. PAUCHARD, B. LIU, G. BAZAN, D. MOSES and A.J. HEEGER; <i>Applied Physics Letters</i> , Vol. 82, Number 22, June 2, 2003.	
CR		"Light Amplification in Polymer Field Effect Transistor Structures", By M. PAUCHARD, J. SWENSEN, D. MOSES and A.J. HEEGER; <i>Journal of Applied Physics</i> , Vol. 94, Number 5, Sept. 1, 2003, pp. 3543	

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.